

ABSTRACT OF THE DISCLOSURE

The invention provides a method for activating impurity element added to a semiconductor and performing gettering process in short time, and a thermal treatment equipment enabling to perform such the heat-treating. The thermal treatment equipment comprises treatment rooms of n pieces ($n > 2$) performing heat-treating, a preparatory heating room, and a cooling room, and heating a substrate using gas heated by heating units of n pieces as a heating source, wherein a gas-supplying unit is connected to a gas charge port of the cooling room, a discharge port of the cooling room is connected to a first gas-heating unit through a heat exchanger, a charge port of an m -th ($1 \leq m \leq (n-1)$) treatment room is connected to a discharge port of an m -th gas-heating unit, a charge port of an n -th treatment room is connected to a discharge port of an n -th gas-heating unit, a discharge port of the n -th treatment room is connected to the heat exchanger, and discharge port of the heat exchanger is connected to gas charge port of the preparatory heating room.